

FEATURES

- Circular Active Area
- Ideal for Electron Detection
- 100% Internal QE
- TO-8 Package

Electro-Optical Characteristics at 25°C

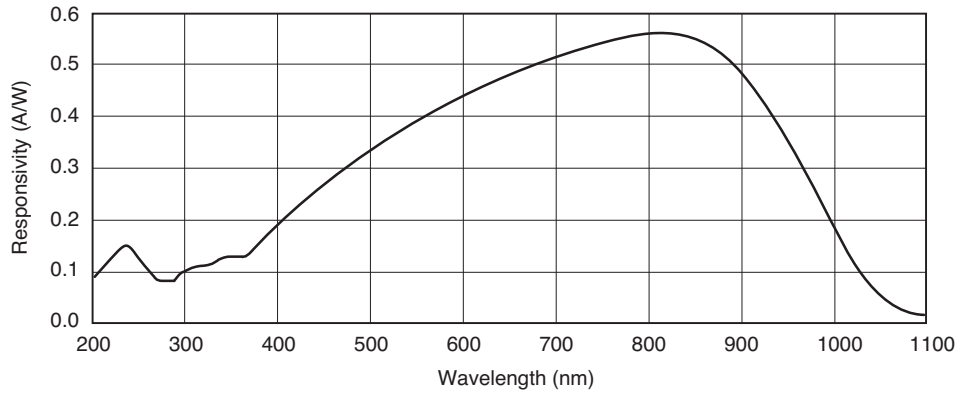
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area ¹	Φ 4.9 mm		19		mm ²
Responsivity	(see graph next page)				A/W
Reverse Breakdown Voltage, V _R	I _R = 1 μA		20		Volts
Capacitance, C	V _R = 0 V		1	3	nF
Rise Time	RL = 50 Ω, V _R = 0 V	0.8	1.7	3.3	usec
Shunt Resistance	V _f = ±10 mV	50	200		MOhms
Dark Current	V _R = 13 V			30	nA

¹ Die active area = Φ5.5 mm, aperture size = Φ4.9 mm.

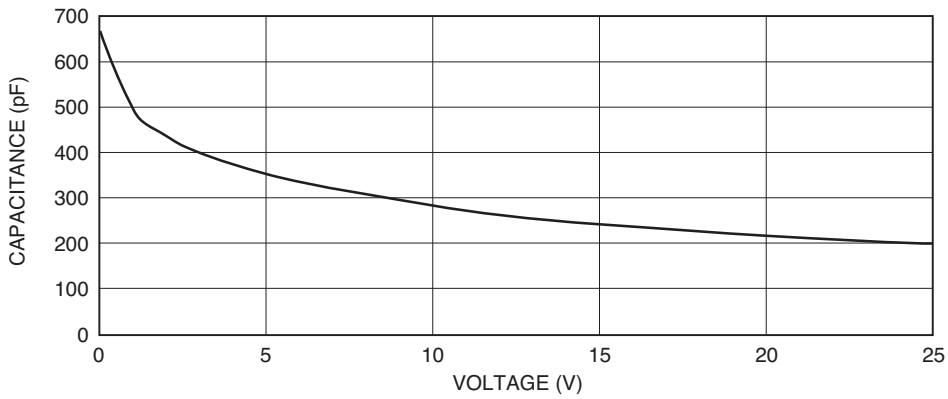
Thermal Parameters

Storage and Operating Temperature Range	Units
Storage Temperature Range	-20°C to 100°C
Operating Temperature Range	20°C to 80°C
Maximum Junction Temperature	100°C
Lead Soldering Temperature ¹	240°C

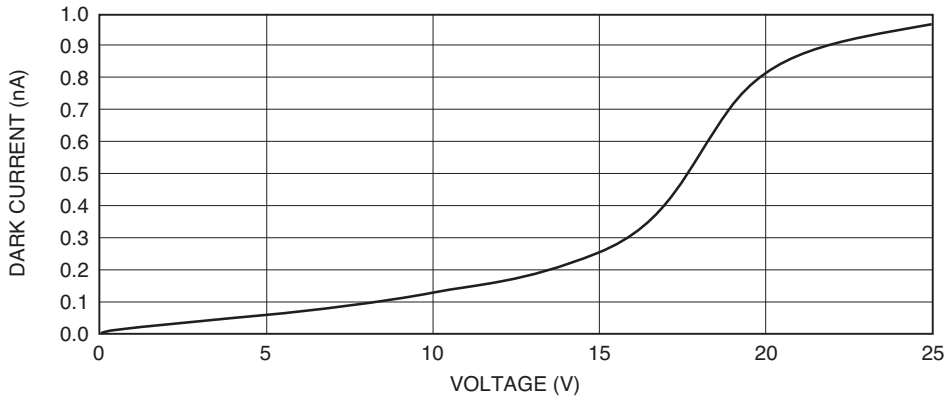
Typical Photon Responsivity



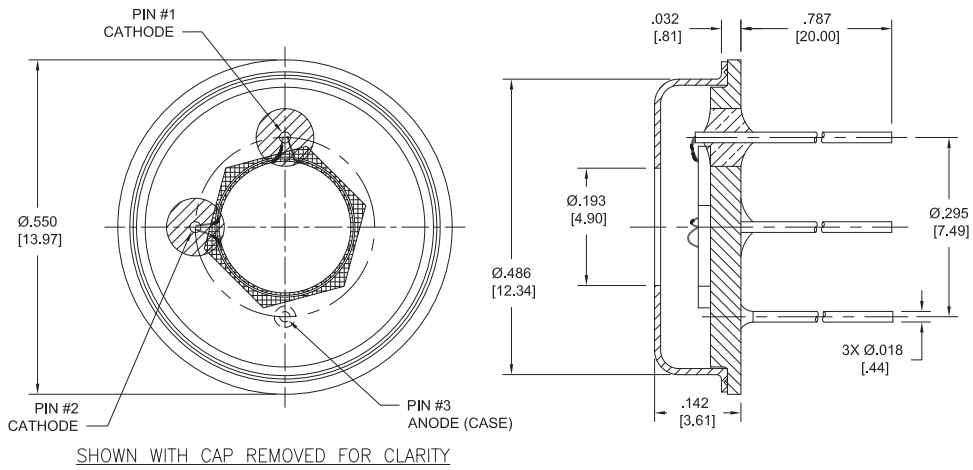
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.